

Improved Standard Products[®]

High Gain, Single N-Channel JFET Amplifier

General Purpose, Low-Noise, Low-Cost, Single N-Channel JFET, Replacement for the BF510

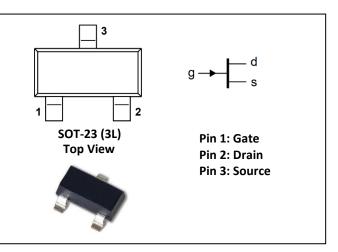
Absolute Maximum Ratings				
@ 25 °C (unless otherwise stated)				
Maximum Temperatures				
Storage Temperature	-65 to +150°C			
Junction Operating Temperature	-55 to +150°C			
Maximum Power Dissipation				
Continuous Power Dissipation @ +25°C	350mW			
Maximum Currents				
Gate Forward Current	$I_{G(F)} = 10 \text{mA}$			
Maximum Voltages				
Gate to Source	$V_{\text{GSS}} = 30V$			
Gate to Drain	$V_{\text{GDS}} = 30V$			



- **Features**
- Low Cutoff Voltage: <2.5V
- High Input Impedance
- Very Low Noise •
- High Gain: AV = 80 @ 20 μA
- Reverse Gate to Source and Drain Voltage ≥ -30V

Benefits

- Low Cost
- Excellent Low Power Supply Operation
- Power Supply: Down to 2.5V
- Low Signal Loss/System Error
- · High System Sensitivity
- High Quality Low-Level Signal



Applications

- High-Gain, Low Noise Amplifiers
- Low-Current, Low-Voltage
- Battery-Powered Amplifiers
- Infrared Detector Amplifiers
- Ultra-High Input Impedance Pre-Amplifiers

Description

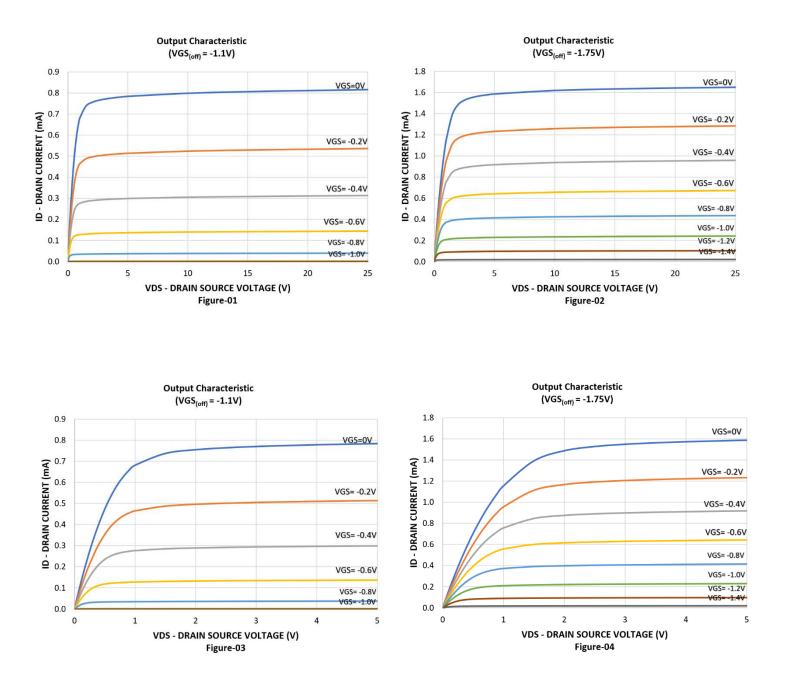
supplies. The LSBF510 is excellent for battery powered

The LSBF510 is a low-cost N-Channel JFET. Features include equipment and low current amplifiers. The TO-236 (SOT-23) low leakage, very low noise, low cutoff voltage (V_{GS(off)} ≤ 2.5V) package provides surface-mount capability. The LSBF510 is and high Gain (Av = 80 V/V) for use with low-level power available in tape-and-reel for automated assembly and in die form for automated assembly.

Electrical Characteristics @ 25 °C (unless otherwise stated)

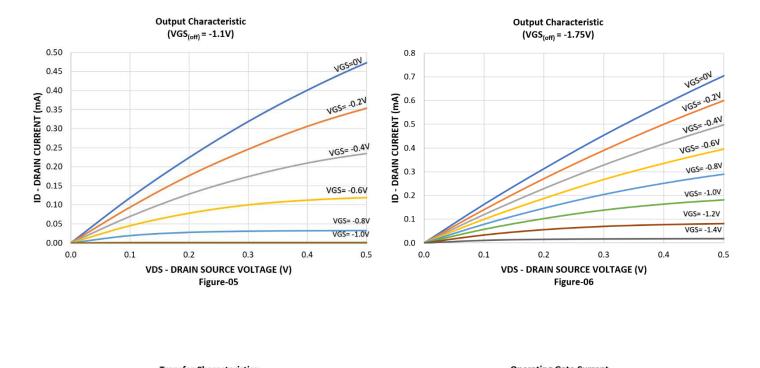
SYMBOL	CHARACTERISTIC	MIN	TYP	MAX	UNITS	CONDITIONS
BV _{GSS}	Gate to Source Breakdown Voltage	-30			V	$I_G = -1\mu A, V_{DS} = 0.0V$
V _{GS(off)}	Gate to Source Cutoff Voltage	-0.3		-2.5		$V_{DS} = 15V, I_D = 10nA$
IDSS	Drain to Source Saturation Current ²	0.2		3.0	mA	$V_{DS} = 15V, V_{GS} = 0.0V$
I _{GSS}	Gate Reverse Current			-200		$V_{GS} = -20V, V_{DS} = 0.0V$
lg	Gate Operating Current		-2		pА	$V_{DG} = 10V, I_D = 0.1mA$
I _{D(off)}	Drain Cutoff Current		2			$V_{DS} = 15V, V_{GS} = 5.0V$
g fs	Forward Transconductance	0.5			mS	$V_{DS} = 15V, V_{GS} = 0.0V, f = 1kHz$
Ciss	Input Capacitance			4.5	pF	$V_{DS} = 15V, V_{GS} = 0.0V, f = 1MHz$
Crss	Reverse Transfer Capacitance		1.3			- , ,
en	Noise Voltage		3.0		nV/√Hz	$V_{DS} = 10V, I_D = 2mA, f = 1kHz$

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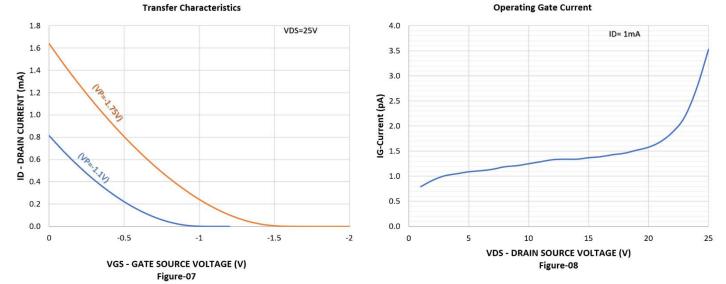


Typical Characteristics

High Gain, Single N-Channel JFET Amplifier



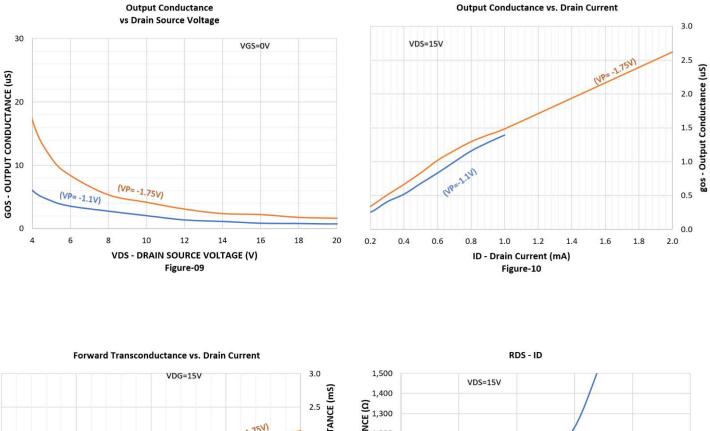
Typical Characteristics Continued

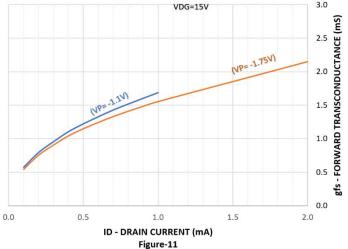


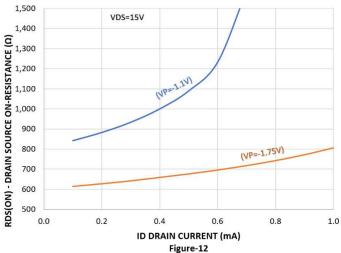
LSBF510

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Typical Characteristics Continued

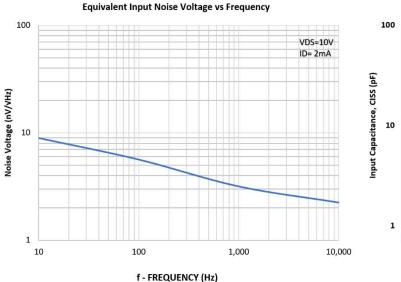


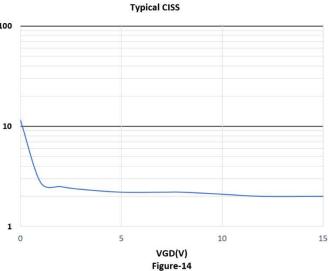




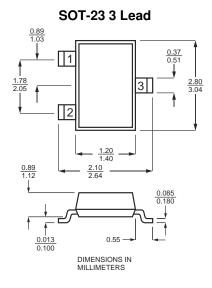
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Package Dimensions



Ordering Information

Notes

- 1. Absolute maximum ratings are limiting values above which serviceability may be impaired.

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 Pulse Test: PW ≤ 300µs, Duty Cycle ≤ 3%
 All characteristics MIN/TYP/MAX numbers are absolute values. Negative values indicate electrical polarity only.
 When ordering include the full Linear Systems part number and package type. Linear Systems creates custom parts on a case by case basis. To learn whether Linear Cycle is a construction of the device specifications to sales@linearsystems.com. One of our constructions of the device specifications to sales@linearsystems.com. Systems can meet your requirements, please send your drawing along with a detailed description of the device specifications to sales@linearsystems.com. One of our qualified representatives will contact you.
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